

General Description

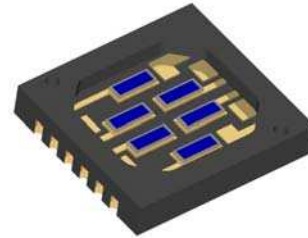
Optical device consisting of a 6 chip silicon N/P photodiode array with high uniformity for the output signals.

The active area of the silicon die is 2.5 x 1.1 mm².

The high optical responsivity is due to the antireflective coating deposited on the photodiode active areas.

The low dark current is good for high temperature applications.

The package type is intended for direct mounting on ceramic or PC boards by manual soldering or SMT.



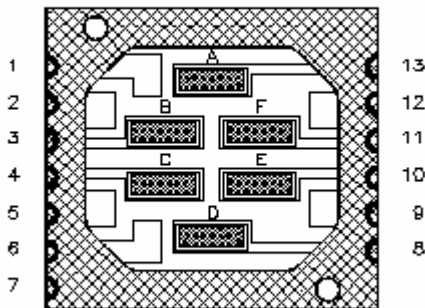
Applications

Incremental Encoders
General Purpose

Features

- High Responsivity = 0.65 A/W (@ $\lambda = 880 \text{ nm}$)
- Low Dark Current
- High photo element area
- Available in SMT Suitable Version
- Compatible with OID10S06
- P/N version available

Pin Functions



No.	Name	Function
1	AK	Photodiode A Cathode
2	BK	Photodiode B Cathode
3	BA	Photodiode B Anode
4	CA	Photodiode C Anode
5	CK	Photodiode C Cathode
6	DK	Photodiode D Cathode
7	BG	Background Contact
8	DA	Photodiode D Anode
9	EK	Photodiode E Cathode
10	EA	Photodiode E Anode
11	FA	Photodiode F Anode
12	FK	Photodiode F Cathode
13	AA	Photodiode A Anode

Ordering Information

OID2	6 Chip Silicon N/P Photodiode Array with Active Area of the Silicon Die 2.5 x 1.1 mm ² .
OID2-PN	6 Chip Silicon P/N Photodiode Array with Active Area of the Silicon Die 2.5 x 1.1 mm ² .

TYPICAL PERFORMANCE CURVES

Figure 1 Spectral Responsivity

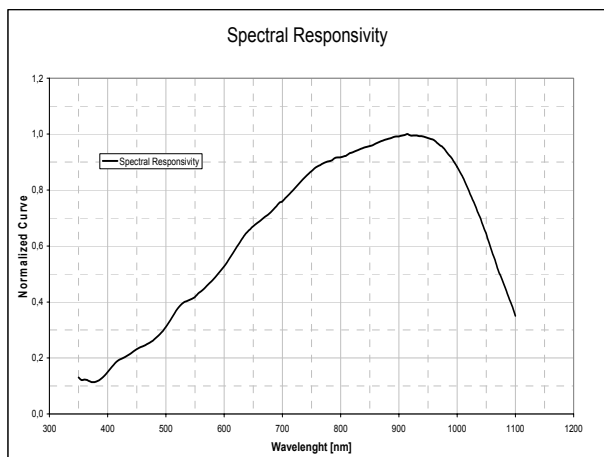


Figure 3 Photocurrent Vs Temperature @ Vr=3 V

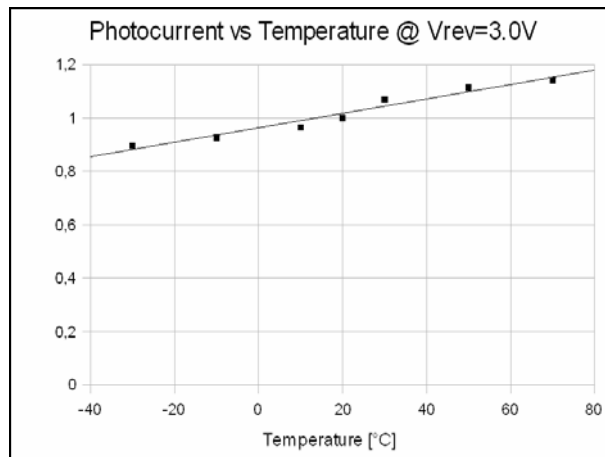


Figure 2 Photocurrent Vs Reverse Voltage

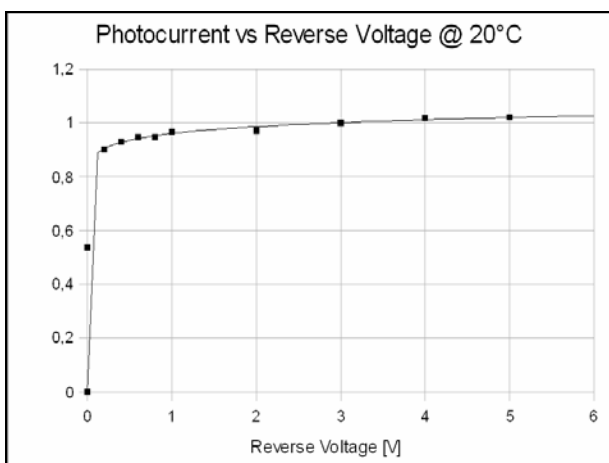


Figure 4 Photocurrent Vs Temperature

